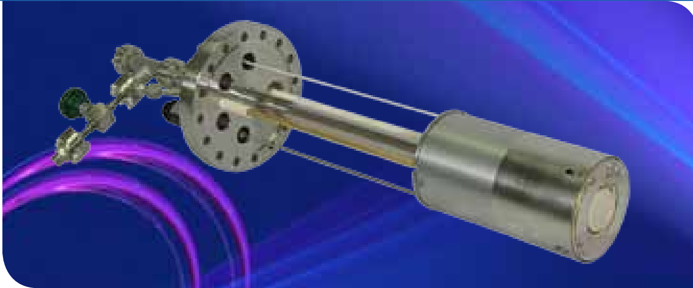
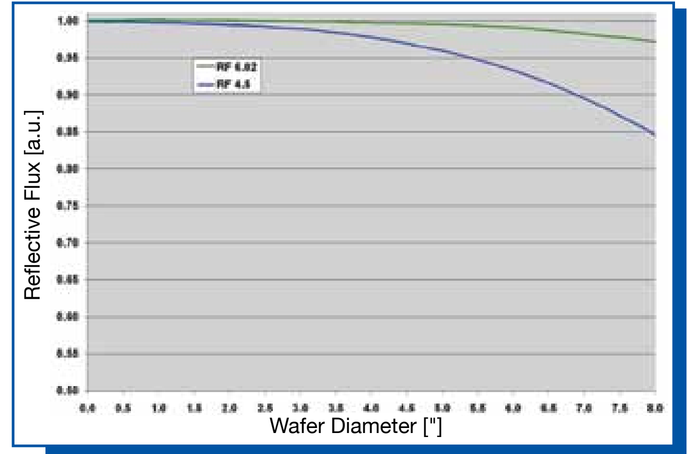
RF-6.02 Plasma Source



Description

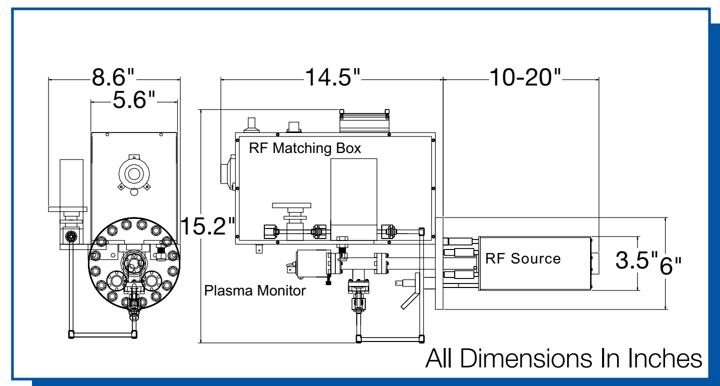
- The RF-6.02 is designed for high volume and large wafer size production systems for nitride and oxide thin film growth.
- Integrated Charge Suppression eliminates the high energy ions from the flux and reduces substrate sputtering.
- The large distribution area of the RF-6.02 is ideal for wafer sizes of 4" or larger.
- With efficient radical generation growth rates greater than 6 μm/hr are achieved under optimal growth conditions.



Relative Flux Distribution of the SVTA-RF-4.5 and SVTA-RF-6.02

Features

- For N_2, O_2, and H_2
- Growth Rates Up to 6 μm/hr
- Flux Uniformity for Wafer Sizes Up to 8" Diameter
- Optical Port for Plasma Monitoring
- Custom Plasma Chamber and Apertures
- Automatic Tuning Matching Network
- Charge Suppression
- Fully Automated Plasma Source with Safety InterLock



All Dimensions In Inches

Specifications

RF Power Level	200 – 2,000 Watts
Gas Flow Rate	0.1 – 10 SCCM
Flange	6.0" CF
Source Diameter	3.50" (89 mm)
Water Cooling	0.5 GPM
Source to Target Distance (Typical)	10.5"
Plasma Chamber	PBN, Alumina

Models	Description
SVTA-RF-6.02PBN	PBN, Specify Length: 10" – 20"
SVTA-RF-6.02ALO	Alumina, Specify Length: 10" – 20"